

**Capsule Thyristor** 

Line	Thyristor
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#### SKT 1800

#### Features

- Hermetic metal case with ceramic insulator
- Capsule package for double sided cooling
- Shallow design with single sided cooling
- Off-state and reverse voltages up to 1600 V
- Amplifying gate

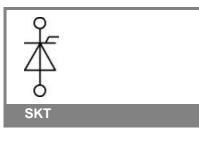
### **Typical Applications**

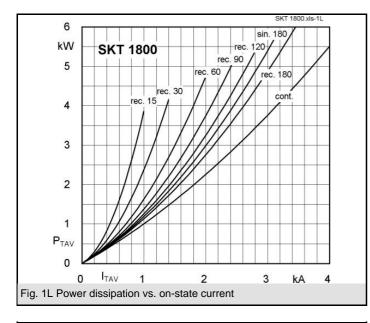
- DC motor control (e. g. for machine tools)
  Controlled rectifiers
- (e. g. for battery charging)
- AC controllers (e. g. for temperature control)
- Soft starters for AC motorsRecommended snubber network

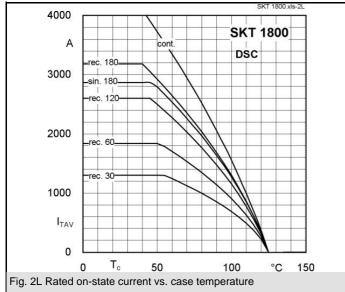
e. g. for V\_{VRMS}  $\leq$  400 V: R = 33  $\Omega/32$  W, C = 1  $\mu F$ 

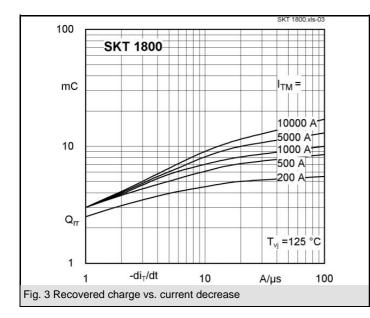
V <sub>RSM</sub>	V <sub>RRM</sub> , V <sub>DRM</sub>	$I_{TRMS}$ = 4500 A (maximum value for continuous operation)	
V	V	$I_{TAV}$ = 1800 A (sin. 180; DSC; $T_c$ = 85 °C)	
1300	1200	SKT 1800/12E	
1500	1400	SKT 1800/14E	
1700	1600	SKT 1800/16E	

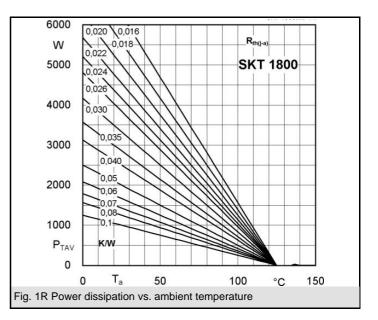
Symbol	Conditions	Values	Units
I <sub>TAV</sub>	sin. 180; T <sub>c</sub> = 100 (85) °C	2500 (1270 )	А
I <sub>D</sub>	2 x N4/250; T <sub>a</sub> = 45 °C; B2 / B6	2500 / 3600	А
	2 x N4/400; T <sub>a</sub> = 45 °C; B2 / B6	2800 /4000	A
I <sub>RMS</sub>	2 x N4/250; T <sub>a</sub> = 45 °C; W1C	2800	А
I <sub>TSM</sub>	T <sub>vj</sub> = 25 °C; 10 ms	53000	А
	T <sub>vj</sub> = 125 °C; 10 ms	45000	А
i²t	T <sub>vj</sub> = 25 °C; 8,3 10 ms	1400000	A²s
	T <sub>vj</sub> = 125 °C; 8,3 10 ms	1000000	A²s
V <sub>T</sub>	T <sub>vj</sub> = 25 °C; I <sub>T</sub> = 3000 A	max. 1,25	V
V <sub>T(TO)</sub>	T <sub>vj</sub> = 125 °C	max. 0,88	V
r <sub>T</sub>	T <sub>vj</sub> = 125 °C	max. 0,124	mΩ
I <sub>DD</sub> ; I <sub>RD</sub>	$T_{vj}$ = 125 °C; $V_{RD}$ = $V_{RRM}$ ; $V_{DD}$ = $V_{DRM}$	max. 100	mA
t <sub>gd</sub>	T <sub>vj</sub> = 25 °C; I <sub>G</sub> = 1 A; di <sub>G</sub> /dt = 1 A/μs	1	μs
t <sub>gr</sub>	V <sub>D</sub> = 0,67 * V <sub>DRM</sub>	2	μs
(di/dt) <sub>cr</sub>	T <sub>vi</sub> = 125 °C	max. 150	A/µs
(dv/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C	max. 1000	V/µs
t <sub>q</sub>	T <sub>vj</sub> = 125 °C	200 300	μs
Ч <sub>Н</sub>	T <sub>vj</sub> = 25 °C; typ. / max.	500 / 1000	mA
I <sub>L</sub>	T <sub>vj</sub> = 25 °C; typ. / max.	2000 / 5000	mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C; d.c.	min. 3	V
I <sub>GT</sub>	$T_{vj} = 25 \text{ °C; d.c.}$	min. 300	mA
$V_{GD}$	$T_{vj} = 125 \ ^{\circ}C; \ d.c.$	max. 0,25	V
I <sub>GD</sub>	T <sub>vj</sub> = 125 °C; d.c.	max. 10	mA
R <sub>th(j-c)</sub>	cont.; DSC	0,015	K/W
R <sub>th(j-c)</sub>	sin. 180; DSC / SSC	0,0155 / 0,033	K/W
R <sub>th(j-c)</sub>	rec. 120; DSC / SSC	0,0165 / 0,0345	K/W
R <sub>th(c-s)</sub>	DSC / SSC	0,003 / 0,006	K/W
T <sub>vj</sub>		- 40 + 125	°C
T <sub>stg</sub>		- 40 + 130	°C
V <sub>isol</sub>		-	V~
F	mounting force	27 34	kN m/s²
a m	approx.	1000	g
		B 19	9
Case		619	

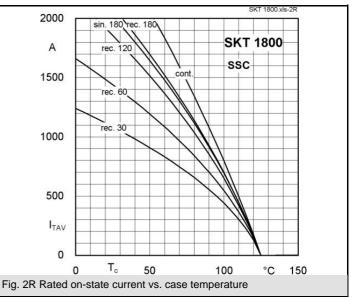


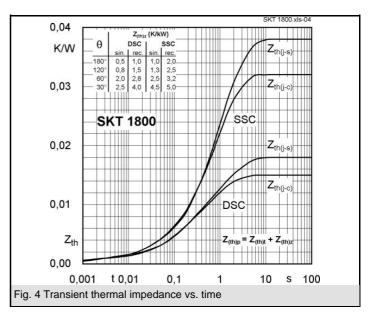


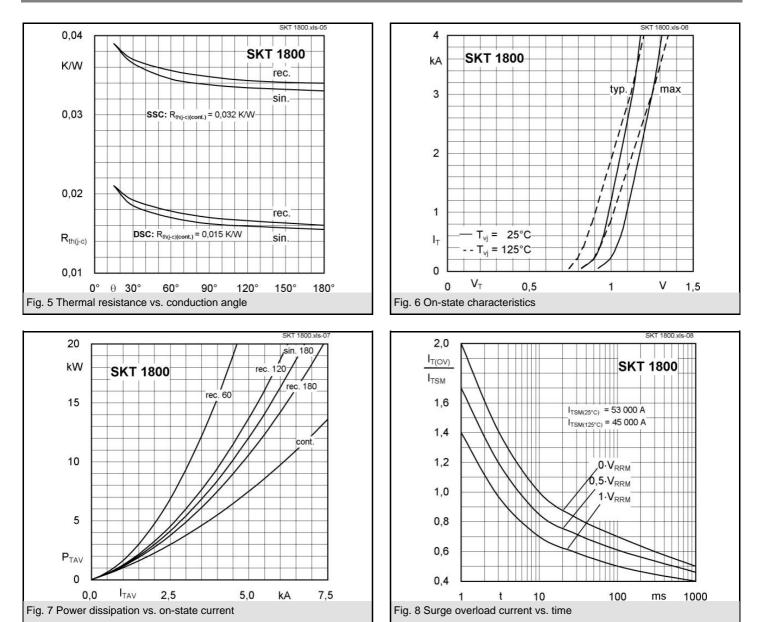


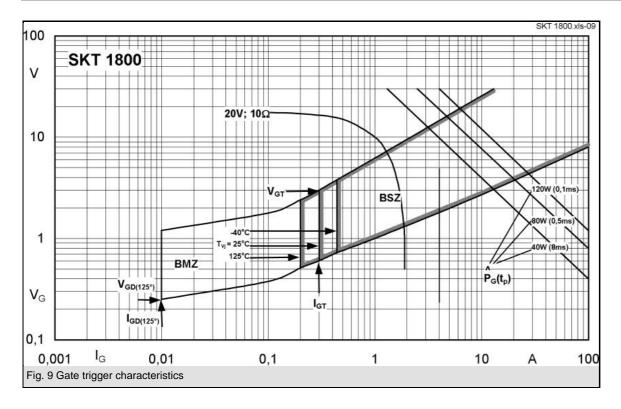


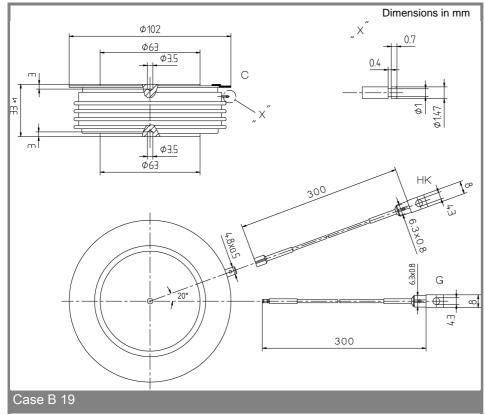












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